

Course: B. Tech.

Branch: E&TC

Semester: VII

Subject Code & Name: BTEXPE703C CMOS Design

Max Marks: 60

Date: 01/02/2023

Duration: 3 Hours

Instructions to the Students:

1. All the questions are compulsory.
2. The level of question/expected answer as per OBE or the Course Outcome (CO) on which the question is based is mentioned in () in front of the question.
3. Use of non-programmable scientific calculators is allowed.
4. Assume suitable data wherever necessary and mention it clearly.

		(Level/CO)	Marks
Q. 1	Solve Any Two of the following.		12
A)	Draw and explain transfer characteristics of CMOS inverter.	1	6
B)	Implement $Y = (A \cdot B + \bar{C} \cdot D) + F$ function using static CMOS design.	2	6
C)	Draw the schematic and layout for two input CMOS NOR gate, Use CMOS Lambda based design rules.	2	6
Q.2	Solve Any Two of the following.		12
A)	Explain various steps involved in CMOS inverter n-well fabrication	1	6
B)	Explain leakage power in CMOS inverter. What are ways to reduce it?	1	6
C)	Implement 4:1 multiplexer using CMOS transmission gates.	2	6
Q. 3	Solve Any Two of the following.		12
A)	Explain Channel length Modulation the non-ideal effect in MOSFET's.	1	6
B)	Write electrical, logical effort, parasitic effort for four input NOR gate.	2	6
C)	Explain CMOS λ -based design rules in detail.	1	6
Q.4	Solve Any Two of the following.		12
A)	Implement JK Flip-Flop using Static CMOS design style.	2	6
B)	Implement $Y = \overline{ABC}$ using dynamic CMOS design style.	2	6
C)	Explain all the parasitic capacitances of the MOSFET in detail	1	6
Q. 5	Solve Any Two of the following.		12
A)	Explain DIBL and subthreshold leakage for MOSFET	1	6
B)	Implement half adder combinational circuit using static CMOS logic.	2	6
C)	Implement two input CMOS AND/NAND gate using Dual rail Dominologic	2	6

***** End *****